

# PUMB3H-Q

50 V, 100 mA PNP/PNP Resistor-Equipped double Transistor; R1 = 4.7 k $\Omega$ , R2 = open

6 May 2021

Product data sheet

# 1. General description

PNP/PNP Resistor-Equipped double Transistor (RET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package.

NPN/NPN complement: PUMH7H-Q NPN/PNP complement: PUMD6H-Q

## 2. Features and benefits

- 100 mA output current capability
- Built-in resistors
- Simplifies circuit design
- · Reduces component count
- Reduces pick and place costs
- High-temperature applications up to 175 °C
- Qualified according to AEC-Q101 and recommended for use in automotive applications

# 3. Applications

- Digital applications
- · Cost saving alternative for BC857 series in digital applications
- Controlling IC inputs
- · Switching loads

## 4. Quick reference data

### Table 1. Quick reference data

| Symbol           | Parameter                 | Conditions               |     | Min | Тур | Max  | Unit |
|------------------|---------------------------|--------------------------|-----|-----|-----|------|------|
| Per transistor   | Per transistor            |                          |     |     |     |      |      |
| V <sub>CEO</sub> | collector-emitter voltage | open base                |     | -   | -   | -50  | V    |
| Io               | output current            |                          |     | -   | -   | -100 | mA   |
| R1               | bias resistor 1           | T <sub>amb</sub> = 25 °C | [1] | 3.3 | 4.7 | 6.1  | kΩ   |

[1] See section "Test information" for resistor calculation and test conditions



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# 5. Pinning information

**Table 2. Pinning information** 

| Pin | Symbol | Description            | Simplified outline                           | Graphic symbol          |
|-----|--------|------------------------|--|-------------------------|
| 1   | GND1   | GND (emitter) TR1      |  | O1 I2 GND2              |
| 2   | I1     | input (base) TR1       | □6 □5 □4                                     |                         |
| 3   | O2     | output (collector) TR2 |  | R1   R2                 |
| 4   | GND2   | GND (emitter) TR2      |  | TR1                     |
| 5   | 12     | input (base) TR2       | H <sub>1</sub> H <sub>2</sub> H <sub>3</sub> | R1                      |
| 6   | O1     | output (collector) TR1 | TSSOP6 (SOT363)                              | GND1 I1 O2<br>006aaa268 |

# 6. Ordering information

**Table 3. Ordering information** 

| Type number | Package |   |         |  |  |
|-------------|---------|---|---------|--|--|
|             | Name    | Description   | Version |  |  |
| PUMB3H-Q    |         | plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body | SOT363  |  |  |

# 7. Marking

Table 4. Marking codes

| Type number | Marking code[1] |
|-------------|-----------------|
| PUMB3H-Q    | 2C%             |

[1] % = placeholder for manufacturing site code

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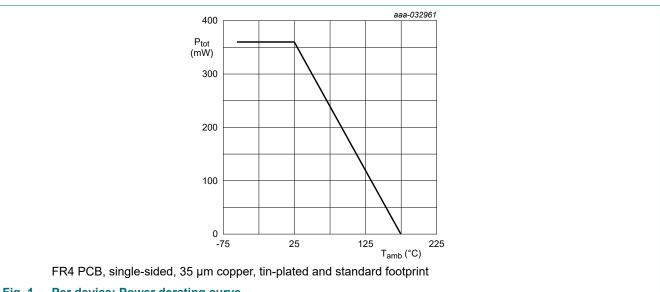
# 8. Limiting values

### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter                 | Conditions               |     | Min | Max  | Unit |
|------------------|---------------------------|--------------------------|-----|-----|------|------|
| Per transiste    | or                        |                          |     |     |      |      |
| V <sub>CBO</sub> | collector-base voltage    | open emitter             |     | -   | -50  | V    |
| V <sub>CEO</sub> | collector-emitter voltage | open base                |     | -   | -50  | V    |
| $V_{EBO}$        | emitter-base voltage      | open collector           |     | -   | -7   | V    |
| V <sub>I</sub>   | input voltage             |                          |     | -30 | 7    | V    |
| Io               | output current            |                          |     | -   | -100 | mA   |
| P <sub>tot</sub> | total power dissipation   | T <sub>amb</sub> ≤ 25 °C | [1] | -   | 240  | mW   |
| Per device       |                           |                          |     |     |      |      |
| P <sub>tot</sub> | total power dissipation   | T <sub>amb</sub> ≤ 25 °C | [1] | -   | 360  | mW   |
| Tj               | junction temperature      |                          |     | -   | 175  | °C   |
| T <sub>amb</sub> | ambient temperature       |                          |     | -55 | 175  | °C   |
| T <sub>stg</sub> | storage temperature       |                          |     | -65 | 175  | °C   |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided, 35 µm copper, tin-plated and standard footprint.



50 V, 100 mA PNP/PNP Resistor-Equipped double Transistor; R1 = 4.7 k $\Omega$ , R2 = open

## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

| Symbol         | Parameter  | Conditions  |     | Min | Тур | Max | Unit |
|----------------|--|-------------|-----|-----|-----|-----|------|
| Per transist   | tor  |             |     |     |     |     | '    |
| $R_{th(j-a)}$  | thermal resistance from junction to ambient      | in free air | [1] | -   | -   | 625 | K/W  |
| $R_{th(j-sp)}$ | thermal resistance from junction to solder point |             |     | -   | -   | 230 | K/W  |
| Per device     | '  |             |     |     | -   | 1   |      |
| $R_{th(j-a)}$  | thermal resistance from junction to ambient      | in free air | [1] | -   | -   | 417 | K/W  |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided, 35 µm copper, tin-plated and standard footprint.

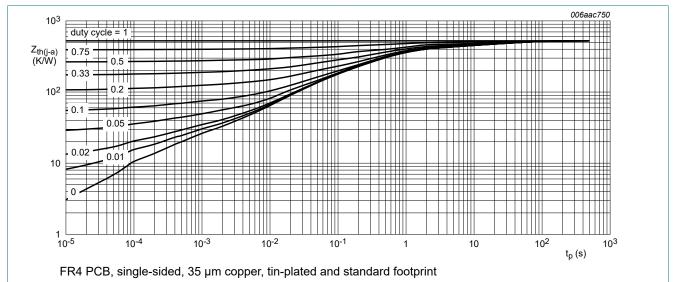


Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

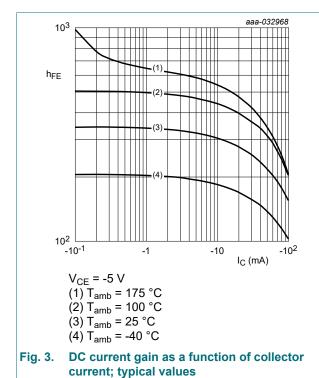
50 V, 100 mA PNP/PNP Resistor-Equipped double Transistor; R1 = 4.7 k $\Omega$ , R2 = open

## 10. Characteristics

**Table 7. Characteristics** 

| Symbol               | Parameter                            | Conditions  |     | Min  | Тур   | Max  | Unit |
|----------------------|--------------------------------------|---|-----|------|-------|------|------|
| Per transist         | or                                   |   |     |      |       |      |      |
| V <sub>(BR)CBO</sub> | collector-base<br>breakdown voltage  | I <sub>C</sub> = -100 μA; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C                                    |     | -50  | -     | -    | V    |
| V <sub>(BR)CEO</sub> | collector-emitter breakdown voltage  | $I_C = -2 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$   |     | -50  | -     | -    | V    |
| I <sub>CBO</sub>     | collector-base cut-off current       | V <sub>CB</sub> = -50 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C                                     |     | -    | -     | -100 | nA   |
| I <sub>CEO</sub>     | collector-emitter cut-off            | V <sub>CE</sub> = -30 V; I <sub>B</sub> = 0 A; T <sub>amb</sub> = 25 °C                                     |     | -    | -     | -100 | nA   |
|                      | current                              | V <sub>CE</sub> = -30 V; I <sub>B</sub> = 0 A; T <sub>amb</sub> = 150 °C                                    |     | -    | -     | -5   | μΑ   |
| I <sub>EBO</sub>     | emitter-base cut-off current         | V <sub>EB</sub> = -7 V; I <sub>C</sub> = 0 mA; T <sub>amb</sub> = 25 °C                                     |     | -    | -     | -100 | nA   |
| h <sub>FE</sub>      | DC current gain                      | $V_{CE}$ = -5 V; $I_{C}$ = -1 mA; $T_{amb}$ = 25 °C   |     | 200  | -     | -    |      |
| V <sub>CEsat</sub>   | collector-emitter saturation voltage | $I_C$ = -10 mA; $I_B$ = -0.5 mA; $T_{amb}$ = 25 °C  |     | -    | -     | -100 | mV   |
| V <sub>I(off)</sub>  | off-state input voltage              | $V_{CE}$ = -5 V; $I_{C}$ = -100 $\mu$ A; $T_{amb}$ = 25 °C  |     | -    | -585  | -500 | mV   |
| V <sub>I(on)</sub>   | on-state input voltage               | $V_{CE}$ = -0.3 V; $I_{C}$ = -10 mA; $T_{amb}$ = 25 °C  |     | -1.3 | -0.88 | -    | V    |
| R1                   | bias resistor 1                      | T <sub>amb</sub> = 25 °C  | [1] | 3.3  | 4.7   | 6.1  | kΩ   |
| C <sub>c</sub>       | collector capacitance                | V <sub>CB</sub> = -10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A;<br>f = 1 MHz; T <sub>amb</sub> = 25 °C |     | -    | -     | 3    | pF   |
| f <sub>T</sub>       | transition frequency                 | $V_{CE}$ = -5 V; $I_{C}$ = -10 mA; f = 100 MHz;<br>$T_{amb}$ = 25 °C  | [2] | -    | 180   | -    | MHz  |

- [1] See section "Test information" for resistor calculation and test conditions
- [2] Characteristics of built-in transistor



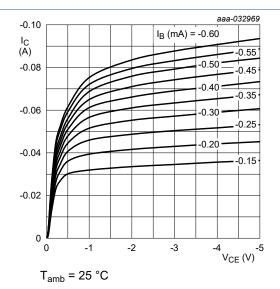
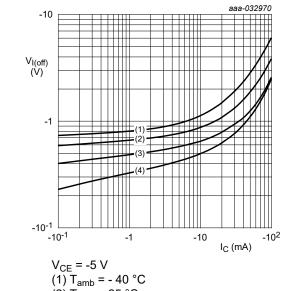


Fig. 4. Collector current as a function of collectoremitter voltage; typical values

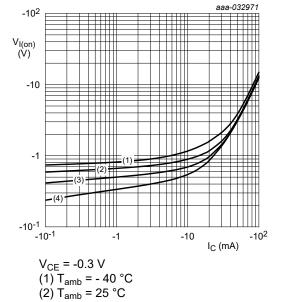
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### 50 V, 100 mA PNP/PNP Resistor-Equipped double Transistor; R1 = 4.7 k $\Omega$ , R2 = open



(2)  $T_{amb} = 25 \, ^{\circ}C$ 

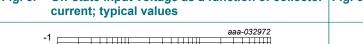
(3) T<sub>amb</sub> = 100 °C (4) T<sub>amb</sub> = 175 °C

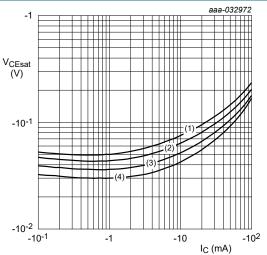


 $(3) T_{amb} = 100 °C$ 

(4)  $T_{amb} = 175 \, ^{\circ}C$ 

Off-state input voltage as a function of collector | Fig. 6. Fig. 5. current; typical values





 $I_{\rm C}/I_{\rm B}=20$ 

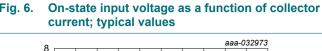
(1)  $T_{amb} = 175 \, ^{\circ}C$ 

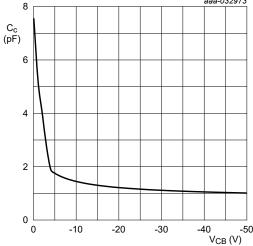
(2)  $T_{amb} = 100 \, ^{\circ}C$ 

(3)  $T_{amb} = 25 \, ^{\circ}C$ 

(4)  $T_{amb} = -40 \, ^{\circ}C$ 

Collector-emitter saturation voltage as a Fig. 7. function of collector current; typical values

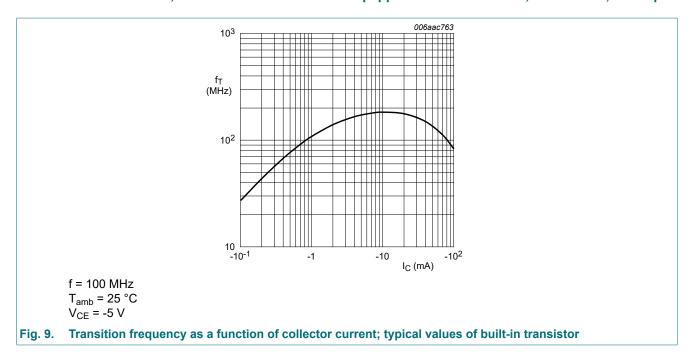




f = 1 MHz $T_{amb} = 25 \, ^{\circ}C$ 

Collector capacitance as a function of collector-Fig. 8. base voltage; typical values

## 50 V, 100 mA PNP/PNP Resistor-Equipped double Transistor; R1 = 4.7 k $\Omega$ , R2 = open



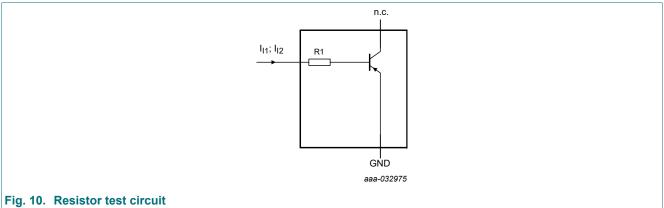
50 V, 100 mA PNP/PNP Resistor-Equipped double Transistor; R1 = 4.7 k $\Omega$ , R2 = open

## 11. Test information

### **Resistor calculation**

Calculation of bias resistor 1 (R1)

$$R_{I} = \frac{V(I_{I2}) - V(I_{I1})}{I_{I2} - I_{I1}}$$



### **Resistor test conditions**

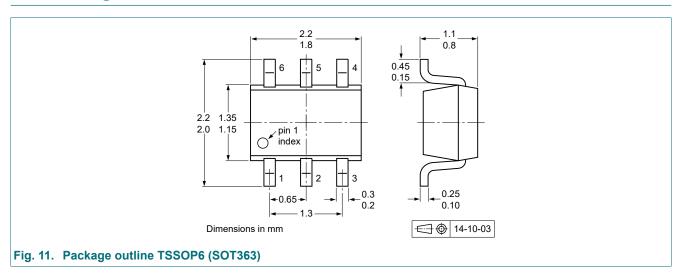
**Table 8. Resistor test conditions** 

| Type number    | R1 (kΩ) | R2 (kΩ) | Test conditions |                 |  |  |  |  |
|----------------|---------|---------|-----------------|-----------------|--|--|--|--|
|                |         |         | I <sub>11</sub> | I <sub>12</sub> |  |  |  |  |
| Per transistor |         |         |                 |                 |  |  |  |  |
| PUMB3H-Q       | 4.7     | open    | -600 µA         | -700 μA         |  |  |  |  |

## **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

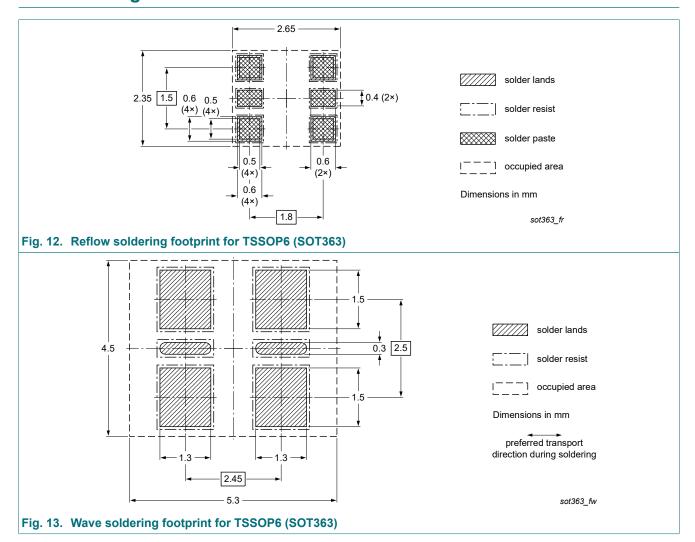
# 12. Package outline



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50 V, 100 mA PNP/PNP Resistor-Equipped double Transistor; R1 = 4.7 k $\Omega$ , R2 = open

# 13. Soldering



50 V, 100 mA PNP/PNP Resistor-Equipped double Transistor; R1 = 4.7 k $\Omega$ , R2 = open

# 14. Revision history

### Table 9. Revision history

| Data sheet ID | Release date |                    | Change notice | Supersedes |
|---------------|--------------|--------------------|---------------|------------|
| PUMB3H-Q v.1  | 20210506     | Product data sheet | -             | -          |

### 50 V, 100 mA PNP/PNP Resistor-Equipped double Transistor; R1 = 4.7 k $\Omega$ , R2 = open

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### **Data sheet status**

| Document status [1][2]         | Product<br>status [3] | Definition  |
|--------------------------------|-----------------------|---|
| Objective [short] data sheet   | Development           | This document contains data from the objective specification for product development. |
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| Product [short]<br>data sheet  | Production            | This document contains the product specification.                                     |

- Please consult the most recently issued document before initiating or completing a design.
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